



GP 2822

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes

Title: SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH

Docket No.: 303.229US2
Filed: August 11, 1998
Examiner: Mark V. Prenty

Serial No.: 09/132,157
Due Date: April 9, 2003
Group Art Unit: 2822

Commissioner for Patents
Washington, D.C. 20231

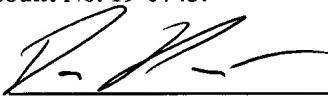
RECEIVED
APR 16 2003
TECHNOLOGY CENTER 2800

We are transmitting herewith the following attached items (as indicated with an "X"):

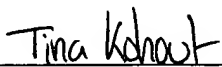
- ☒ A return postcard.
☒ An Amendment and Response (10 Pages).


Please consider this a **PETITION FOR EXTENSION OF TIME** for sufficient number of months to enter these papers and please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938, Minneapolis, MN 55402 (612-373-6900)

By: 
Atty: David C. Peterson
Reg. No. 47,857

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on this 9 day of April, 2003.


Name


Signature

Customer Number 21186

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
(GENERAL)

P.O. Box 2938, Minneapolis, MN 55402 (612-373-6900)

S/N 09/132157

PATENT

*Response
#39
Filer
4/14/03*

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes

Examiner: Mark Prenty

Serial No.: 09/132157

Group Art Unit: 2822

Filed: August 11, 1998

Docket No.: 303.229US2

Title: SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION
IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH

AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

Commissioner for Patents
Washington, D.C. 20231

Applicant has reviewed the Office Action mailed on January 9, 2003. Please enter the following remarks.